

ABSTRACT

Provided herein may be a semiconductor memory device and a method of operating the same. By the method, at least one normal program loop may be performed on a first memory cell, among a plurality
5 of memory cells included in a page selected as a program target, having an N-th program state, among a plurality of program states, as a target program state, and at least one blind program loop may be performed on the first memory cell. While the at least one blind program loop is being performed, a target data pattern that is stored in a data latch of a first page
10 buffer coupled to the first memory cell and that corresponds to the N-th program state may be changed to a first data pattern corresponding to a first program state that is lower than the N-th program state, and wherein N is a natural number equal to or greater than 2.

15 FIG. 10